

Growing and characterization of YBaCo₄O_{7+δ} thin films on (1022)-oriented sapphire substrates.

J. F. Montoya⁽¹⁾, J. L. Izquierdo^{(1)*}, A. Gomez⁽²⁾, O. Arnache⁽³⁾, J. Osorio⁽³⁾, J. Marín⁽¹⁾, and O. Morán⁽¹⁾

(1) Laboratorio de Materiales Cerámicos y Vítreos, Departamento de Física, Universidad Nacional de Colombia, Sede Medellín, A.A. 568, Medellín, Colombia

(2) Departamento de Ingeniería de Materiales, Universidad Nacional de Colombia, sede Medellín, A.A. 568, Medellín, Colombia

(3) Grupo de Estado Sólido, Departamento de Física, Universidad del Antioquia, A.A. 25360 Cali, Colombia

* Corresponding author: e-mail: jlizquierdon@unalmed.edu.co

Abstract – Successful growth of thin films of the novel cobaltite YBaCo₄O_{7+δ} on (1022)-oriented sapphire substrates is reported. This is the first time that this novel cobaltite is produced in form of thin film. Samples were fabricated using dc sputtering system working at high oxygen pressures. Films were characterized after their structural, morphological and electrical properties. X-ray diffraction analysis showed textured growth of the films on the sapphire substrates. Measurements of the resistivity as a function of the temperature revealed semiconducting character of the as grown films. No indication of transitions was detected in the measuring temperature range (50-300 K).

Recently, Co-based compounds have intensively been investigated due to the existence of intriguing magnetic properties [1]. The most representative element of such cobalt oxide systems is the spinel Co₃O₄ which features antiferromagnetic ordering [2]. Recently, the new type of ceramic compound YBaCo₄O₇, denoted 114, was reported to exhibit an unusual magnetic behavior, which resembled that of a spin-glass [3] phase. Also, the structure itself seems to be a geometrically frustrated system, which has a unique magnetic substructure. Certainly, the YBaCo₄O₇ lattice comprises layers formed by two different types of cobalt-oxygen tetrahedral, (Co1)O₄ and (Co2)O₄, which are connected by corners and characterized by different bond lengths. Such a feature was interpreted as favoring actual ordering of the cobalt cations in different oxidation states [4]. On the other hand, the conductivity of YBaCo₄O₇ ceramics seems to be predominantly p-type electronic and it is essentially *p*(O₂)-independent. The mentioned results have been achieved in polycrystalline YBaCo₄O₇ samples. Nevertheless, no information on the properties of this compound in form of thin film is available in literature yet. Therefore, the aim of the present work is to study the structural, transport and magnetic properties of YBaCo₄O₇ thin films. The films were fabricated using a dc sputtering system working at high oxygen pressures. The films were characterized after their structural, morphological, magnetic and electrical properties. X-ray diffraction analysis showed a textured growth on the sapphire substrates. Despite the high growth temperature (800°C) no indication of interface reaction (formation of BaAlO₄ or Y₂O₃) was detected.

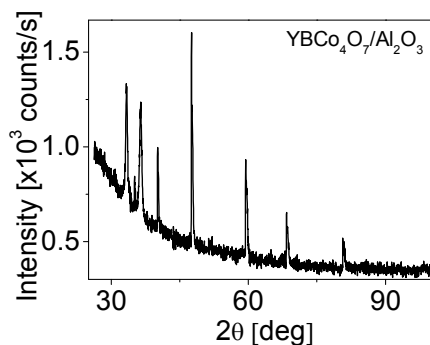


Figure 1: XRD pattern of an ~ 200 nm thin YBaCo₄O₇ film deposited on an Al₂O₃ substrate by high-oxygen pressure dc sputtering.

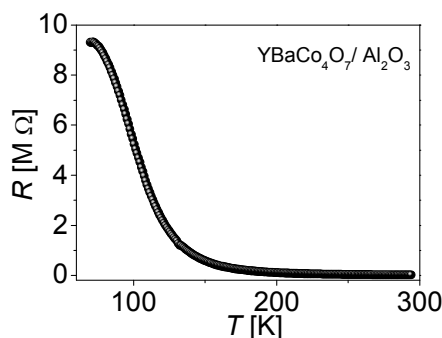


Figure 2: Temperature dependence of the resistance of an YBaCo₄O₇ film on Al₂O₃.

[1] C. Pinta, D. Fuchs, M. Merz, M. Wissinger, E. Arac, H. v. Löhneysen, A. Samartsev, P. Nagel, and S. Schuppler, Phys. Rev. B **78** (2008)174402.

[2] W.L. Roth, J. Phys. Chem. Solids **25** (1964) 1.

[3] M. Valldor, Solid State Sci. **6** (2004) 251.

[4] D.V. Sheptyakov, A. Podlesnyak, S.N. Barilo, S.V. Shiryayev, D.D. Khalyavin, D.Yu. Chernyshov, N.I. Leonyuk, PSI Sci. Rep. **3** (2001) 64.